# PLL Clock Multiplier, 14 MHz - 200 MHz, 3.3 V / 5.0 V

# **Description**

The NB3N511 is a clock multiplier that will generate one of nine selectable output multiples of an input frequency via two 3-level select inputs (S0, S1). It accepts a standard fundamental mode crystal or an external reference clock signal. Phase-Locked-Loop (PLL) design techniques are used to produce a low jitter, TTL level clock output up to 200 MHz with a 50% duty cycle. An Output Enable (OE) pin is provided, and when asserted low, the clock output goes into tri-state (high impedance). The NB3N511 is commonly used in electronic systems as a cost efficient replacement for crystal oscillators

#### **Features**

- Clock Output Frequencies up to 200 MHz
- Nine Selectable Multipliers of the Input Frequency
- Operating Range:  $V_{DD} = 3.3 \text{ V} \pm 10\% \text{ or } 5.0 \text{ V} \pm 5\%$
- Low Jitter Output of 25 ps One Sigma (rms)
- Zero ppm Clock Multiplication Error
- 45% 55% Output Duty Cycle
- TTL/CMOS Output with 25 mA TTL Level Drive
- Crystal Reference Input Range of 5 32 MHz
- Input Clock Frequency Range of 1 50 MHz
- OE, Output Enable with Tri-State Output
- 8-Pin SOIC
- Industrial Temperature Range -40°C to +85°C
- These are Pb-Free Devices



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### **MARKING DIAGRAM**



SOIC-8 D SUFFIX CASE 751

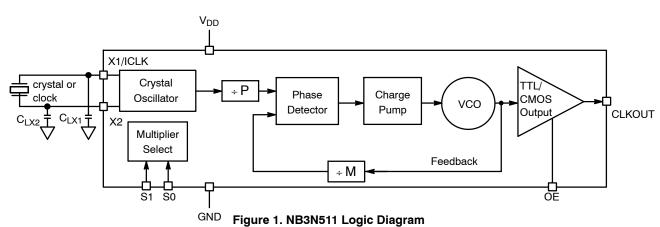


3N511 = Specific Device Code A = Assembly Location

L = Wafer Lot Y = Year W = Work Week ■ Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.



**Table 1. CLOCK MULTIPLIER SELECT TABLE** 

S1*	S0*	CLKOUT Multiplier
L	L	4X Input
L	М	5.333X Input
L	Н	5X Input
М	L,	2.5X Input
М	М	2X Input
M	Н	3.333X Input
Н	L,	6X Input
Н	М	3X Input
Н	Н	8X Input

X1/ICLK 1 8 X2

V<sub>DD</sub> 2 7 OE

GND 3 6 S0

S1 4 5 CLKOUT

Figure 2. NB3N511 Package Pinout, 8-Pin (150 mil) SOIC (Top View)

L = GND

H = VDD

M = OPEN (unconnected; will default to VDD/2)

**Table 2. PIN DESCRIPTION** 

Pin#	Name	I/O	Description
1	X1/ICLK	Crystal or LVCMOS/LVTTL Input	Crystal or external reference clock input
2	VDD	Power supply	Positive supply voltage
3	GND	Power supply	0 V. Ground.
4	S1	Three level Input	Multiplier select pin – connect to V <sub>DD</sub> , GND or float
5	CLKOUT	LVCMOS/LVTTL Output	Clock output
6	S0	Three level Input	Multiplier select pin – connect to V <sub>DD</sub> , GND or float
7	OE	LVCMOS/LVTTL Input	Output Enable. CLKOUT is high impedance when OE is low. Internal pullup
8	X2	Crystal	Crystal input – Leave open when providing an external clock reference

Table 3. COMMON OUTPUT FREQUENCY EXAMPLES

Output Frequency (MHz)	Input Frequency (MHz)	S1, S0
20	10	M, M
24	12	M, M
30	10	H, M
32	16	M, M
33.33	16.66	M, M
37.5	15	M, L
40	10	L, L
48	12	L, L
50	20	M, L
60	10	H, L
64	16	L, L

Table 4. COMMON OUTPUT FREQUENCY EXAMPLES

Output Frequency (MHz)	Input Frequency (MHz)	S1, S0
66.66	20	M, H
72	12	H, L
75	25	H, M
80	10	H, H
83.33	25	M, H
90	15	H, L
100	20	L, H
120	15	H, H
125	25	L, H
133.3	25	L, M
150	25	H, L

<sup>\*</sup>Pins S1 and S0 default to M when open

**Table 4. ATTRIBUTES** 

Characterist	Value			
ESD Protection	Human Body Model Machine Model Charged Device Model	> 1 kV > 150 V > 1 kV		
RPU - OE Input Pull-up Resistor		270 kΩ		
Moisture Sensitivity (Note 1)	SOIC-8	Level 1		
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V 0 @ 0.125 in		
Transistor Count		9555		
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test				

<sup>1.</sup> For additional information, see Application Note AND8003/D.

# **Table 5. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
$V_{DD}$	Positive Power Supply	GND = 0 V		7	V
V <sub>IO</sub>	Input and Output Voltages			$-0.5 \text{ V} \le \text{V}_{10} \le \text{V}_{DD} + 0.5$	V
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
θЈА	Thermal Resistance (Junction-to-Ambient)	0 Ifpm 500 Ifpm	SOIC-8 SOIC-8	190 130	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 2)	SOIC-8	41 to 44	°C/W
T <sub>sol</sub>	Wave Solder Pb-Free			265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power) with 8 filled thermal vias under exposed pad.

Table 6. DC CHARACTERISTICS  $V_{DD} = 3.3 \text{ V} \pm 10\%$  or  $5.0 \text{ V} \pm 5\%$  unless otherwise noted, GND = 0 V,  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ 

Symbol	Characteristic		Min	Тур	Max	Unit
$V_{DD}$	Operating Voltage $V_{DD}$ $V_{DD}$ =	= 5 V 3.3 V	4.75 3.0		5.25 3.6	V
I <sub>DD</sub>	Power Supply Current – Inputs and outputs open, CLKOUT opera at 100 MHz (with 20 MHz crystal) $V_{DD}$ =	= 5 V		9 8		mA
V <sub>OH</sub>	Output HIGH Voltage I <sub>OH</sub> = -4 mA CMOS High		V <sub>DD</sub> – 0.4			V
V <sub>OH</sub>	Output HIGH Voltage I <sub>OH</sub> = -25 mA TTL High		2.4			V
V <sub>OL</sub>	Output LOW Voltage I <sub>OL</sub> = 25 mA				0.4	V
V <sub>IH</sub>	Input HIGH Voltage, ICLK only (pin 1) $V_{DD}$ $V_{DD} =$	= 5 V 3.3 V	$(V_{DD}/2) + 1$ $(V_{DD}/2) + 0.7$			V
V <sub>IL</sub>	Input LOW Voltage, ICLK only (pin 1) $V_{DD}$ $V_{DD} =$	= 5 V 3.3 V			(V <sub>DD</sub> / 2) – 1 (V <sub>DD</sub> / 2) – 0.7	V
V <sub>IH</sub>	Input HIGH Voltage, S0, S1		V <sub>DD</sub> – 0.5			V
$V_{IL}$	Input LOW Voltage, S0, S1				0.5	V
V <sub>IH</sub>	Input HIGH Voltage, OE (pin 7)		2.0			V
$V_{IL}$	Input LOW Voltage, OE (pin 7)				0.8	V
C <sub>in</sub>	Input Capacitance, S0, S1 and OE			4		pF
I <sub>SC</sub>	Output Short Circuit Current, CLKOUT			±70		mA
	Nominal Output Impedance			20		Ω

 $\textbf{Table 7. AC CHARACTERISTICS} \ V_{DD} = 3.3 \ V \pm 10\% \ or \ 5.0 \ V \pm 5\% \ unless \ otherwise \ noted, \ GND = 0 \ V, \ T_{A} = -40 ^{\circ}C \ to \ +85 ^{\circ}C$ 

Symbol	Characteristic	Min	Тур	Max	Unit
f <sub>Xtal</sub>	Crystal Input Frequency (Note 3)	5		32	MHz
f <sub>CLKIN</sub>	Clock Input Frequency	1		50	MHz
fоит	Output Frequency Range $f_{OUTMIN} \le f_{IN}$ x Multiplier $\le f_{OUTMAX}$ $V_{DD} = 4.25$ to $5.25$ V $(5.0$ V $\pm$ 5%) $V_{DD} = 3.0$ to $3.6$ V $(3.3$ V $\pm$ 10%)	4 4		200 200	MHz
DC	Output Clock Duty Cycle at 1.5 V	45	50	55	%
OE <sub>H</sub>	Output enable time, OE high to output on		50		ns
OE <sub>L</sub>	Output disable time, OE low to tri-state		50		ns
t <sub>jitter (rms)</sub>	Period Jitter (rms, 1 σ)		25		ps
tjitter (pk-to-pk)	Total Period Jitter, (peak-to-peak)		±70		ps
t <sub>r</sub> /t <sub>f</sub>	Output rise/fall time (0.8 V to 2.0 V) (measured with 15 pF load)		1	1.5	ns

<sup>3.</sup> The crystal should be fundamental mode, parallel resonant. Do not use third overtone. For exact tuning when using a crystal, capacitors should be connected from pins X1/CLK to GND and X2 to GND. The value of these capacitors is given by the following equation, where C<sub>L</sub> is the specified crystal load capacitance: Crystal capacitance (pF) = (C<sub>L</sub> – 12) X 2. So, for a crystal with 16 pF load capacitance, use two 8 pF capacitors.

#### **APPLICATIONS INFORMATION**

# **High Frequency CMOS/TTL Oscillators**

The NB3N511, along with a low frequency fundamental mode crystal, can build a high frequency TTL output oscillator. For example, a 20 MHz crystal connected to the NB3N511 with the 5X output selected (S1 = L, S0 = H) produces an 100 MHz CMOS/TTL output clock.

### **Decoupling and External Components**

The NB3N511 requires a 0.01  $\mu F$  decoupling capacitor to be connected between  $V_{DD}$  and GND on pins 2 and 3. It must be connected close to the NB3N511 to minimize lead inductance. Control input pins can be connected to device pins  $V_{DD}$  or GND, or to the  $V_{DD}$  and GND planes on the board.

#### **Series Termination Resistor**

A 33  $\Omega$  terminating resistor can be used next to the CLK pin for trace lengths over one inch.

### **Crystal Information**

The crystal used should be a fundamental mode (do not use third overtone), parallel resonant. Crystal load capacitors should be connected from pins X1 to ground and X2 to ground to optimize the frequency accuracy, See Figure 1.

The total on chip capacitance is approximately 12 pF. A parallel resonant, fundamental mode crystal should be used. The device crystal connections should include pads for

small capacitors from X1 to ground and from X2 to ground. These capacitors are used to adjust the stray capacitance of the board to match the nominally required crystal load capacitance. Because load capacitance can only be increased in this trimming process, it is important to keep stray capacitance to a minimum by using very short PCB traces (and no vias) between the crystal and device. Crystal capacitors, if needed, must be connected from each of the pins X1 and X2 to ground. The value (in pF) of these crystal caps should equal  $(C_L - 12 \text{ pF}) * 2$ . In this equation,  $C_L = \text{crystal}$  load capacitance in pF. Example: For a crystal with a 16 pF load capacitance, each crystal capacitor would be 8 pF [ $(16 - 12) \times 2 = 8$ ].

**Table 8. RECOMMENDED CRYSTAL PARAMETERS** 

Parameter	Value
Crystal Cut	Fundamental AT Cut
Resonance	Parallel Resonance
Load Capacitance	18 pF
Operating Range	–40 to +85°C
Shunt Capacitance	5 pF Max
Equivalent Series Resistance (ESR)	50 Ω Max
Correlation Drive Level	1.0 mW Max

#### **ORDERING INFORMATION**

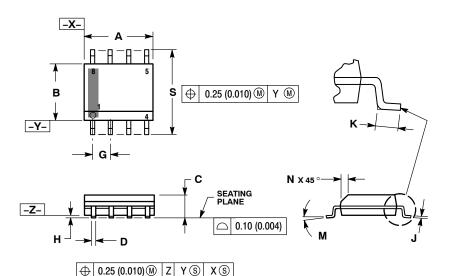
Device	Package	Shipping <sup>†</sup>
NB3N511DG	SOIC-8 (Pb-Free)	98 Units / Rail
NB3N511DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SOIC-8 NB CASE 751-07 **ISSUE AK** 

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.05	0 BSC
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

# **SOLDERING FOOTPRINT\***



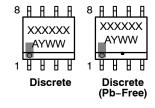
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

# **STYLES ON PAGE 2**

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# DATE 16 FEB 2011

			27112 101 22 2
STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DHAIN 1  STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	a COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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